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Fairchild Semiconductor FDS86252

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April 2011

# FDS86252

# N-Channel Power Trench<sup>®</sup> MOSFET 150 V, 4.5 A, 55 m $\Omega$

#### **Features**

- Max  $r_{DS(on)}$  = 55 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 4.5 A
- Max  $r_{DS(on)}$  = 80 m $\Omega$  at  $V_{GS}$  = 6 V,  $I_D$  = 3.7 A
- High performance trench technology for extremely low r<sub>DS(on)</sub>
- High power and current handling capability in a widely used surface mount package
- 100% UIL Tested
- RoHS Compliant

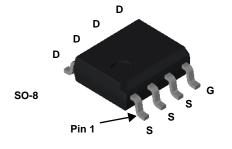


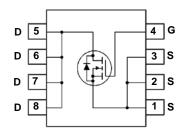
#### **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintaiin superior switching performance.

#### Application

■ DC-DC Conversion





## **MOSFET Maximum Ratings** $T_A = 25$ °C unless otherwise noted

Symbol	Parameter			Ratings	Units
$V_{DS}$	Drain to Source Voltage			150	V
$V_{GS}$	Gate to Source Voltage			±20	V
	Drain Current -Continuous			4.5	^
'D	-Pulsed			20	A
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	60	mJ
Б	Power Dissipation T <sub>A</sub>	<sub>λ</sub> = 25 °C	(Note 1)	5.0	14/
$P_{D}$	Power Dissipation T <sub>A</sub>	(= 25 °C	(Note 1a)	2.5	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	1		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Package Reel Size		Quantity
FDS86252	FDS86252	SO-8	13 "	12 mm	2500 units



# Distributor of Fairchild Semiconductor: Excellent Integrated System Limited

Datasheet of FDS86252 - MOSFET N-CH 150V 4.5A 8SOIC

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### **Electrical Characteristics** T<sub>J</sub> = 25 °C unless otherwise noted

Symbol	Parameter Test Conditions		Min	Тур	Max	Units
Off Chara	acteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		103		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2	3.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25 °C		-11		mV/°C
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A		45	55	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 3.7 \text{ A}$		57	80	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A, T <sub>J</sub> = 125 °C		86	105	
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 4.5 \text{ A}$		13		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 75.V.V 0.V	718	955	pF
Coss	Output Capacitance	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	77	105	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 = 1 101112	3.3	5	pF
R <sub>a</sub>	Gate Resistance		0.6		Ω

#### **Switching Characteristics**

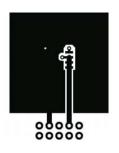
t <sub>d(on)</sub>	Turn-On Delay Time				9.2	19	ns
t <sub>r</sub>	Rise Time		$V_{DD} = 75 \text{ V}, I_{D} = 4.5 \text{ A},$ $V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		1.6	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10 V, R <sub>GEN</sub> =			14	24	ns
t <sub>f</sub>	Fall Time				2.9	10	ns
0	Total Gate Charge	$V_{GS} = 0 \text{ V to } 10 \text{ V}$			10.6	15	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to 5 V}$	V <sub>DD</sub> = 75 V		5.2	9	nC
$Q_{gs}$	Total Gate Charge		I <sub>D</sub> = 4.5 A		3.5		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				2.3		nC

### **Drain-Source Diode Characteristics**

V	/sp   Source to Drain Dioge Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 4.5 \text{ A}$ (Note 2)		0.80	1.3	V
v <sub>SD</sub>		$V_{GS} = 0 \text{ V}, I_S = 2 \text{ A}$ (Note 2)		0.76	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 4.5 A, di/dt = 100 A/μs		60	95	ns
Q <sub>rr</sub>	Reverse Recovery Charge			74	118	nC

#### NOTES

<sup>1.</sup> R<sub>0JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0JC</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.



a) 50 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b) 125 °C/W when mounted on a minimum pad.

- 2. Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0 %.
- 3. Starting T  $_{J}$  = 25 °C; N-ch: L = 1 mH, I  $_{AS}$  = 11 A, V  $_{DD}$  = 135 V, V  $_{GS}$  = 10 V.



Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

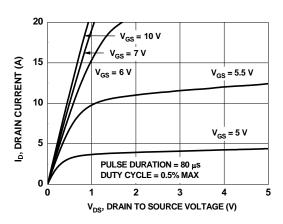


Figure 1. On-Region Characteristics

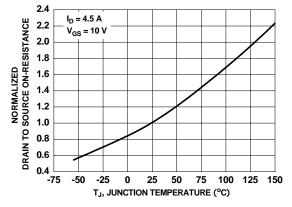


Figure 3. Normalized On-Resistance vs Junction Temperature

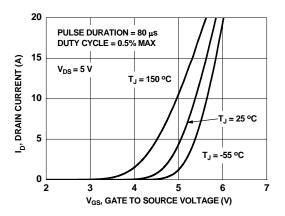


Figure 5. Transfer Characteristics

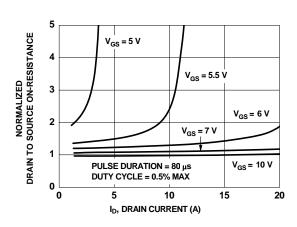


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

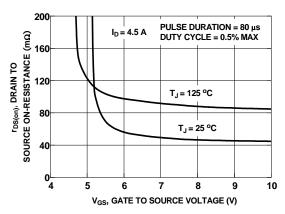


Figure 4. On-Resistance vs Gate to Source Voltage

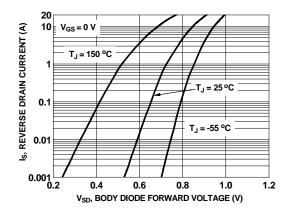


Figure 6. Source to Drain Diode Forward Voltage vs Source Current



#### Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

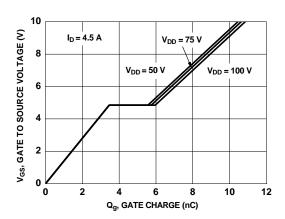


Figure 7. Gate Charge Characteristics

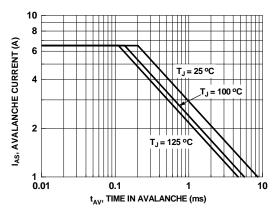


Figure 9. Unclamped Inductive Switching Capability

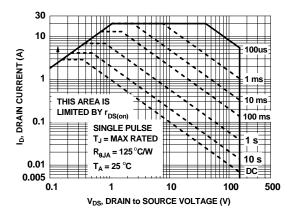


Figure 11. Forward Bias Safe Operating Area

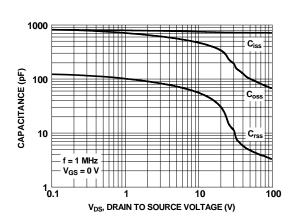


Figure 8. Capacitance vs Drain to Source Voltage

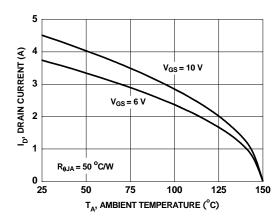


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

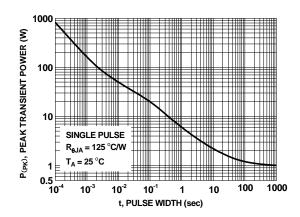


Figure 12. Single Pulse Maximum Power Dissipation

### Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

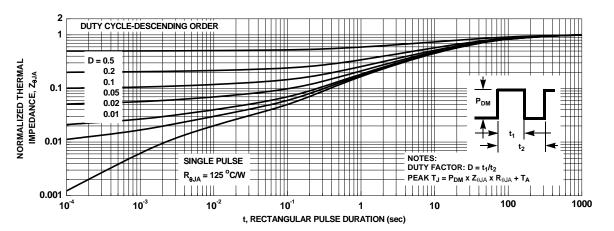


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

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Datasheet of FDS86252 - MOSFET N-CH 150V 4.5A 8SOIC

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